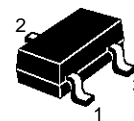


SMALL SIGNAL PNP TRANSISTORS

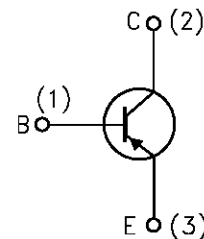
Type	Marking
BCW69	H1
BCW70	H2

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- LOW LEVEL AUDIO AMPLIFICATION AND SWITCHING



SOT-23

INTERNAL SCHEMATIC DIAGRAM



SC08810

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	-50	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-45	V
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-50	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-0.1	A
I_{CM}	Collector Peak Current	-0.2	A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	300	mW
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

BCW69/BCW70

THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	420	$^{\circ}\text{C}/\text{W}$
---------------	-------------------------------------	-----	-----	-----------------------------

• Mounted on a ceramic substrate area = 10 x 8 x 0.6 mm

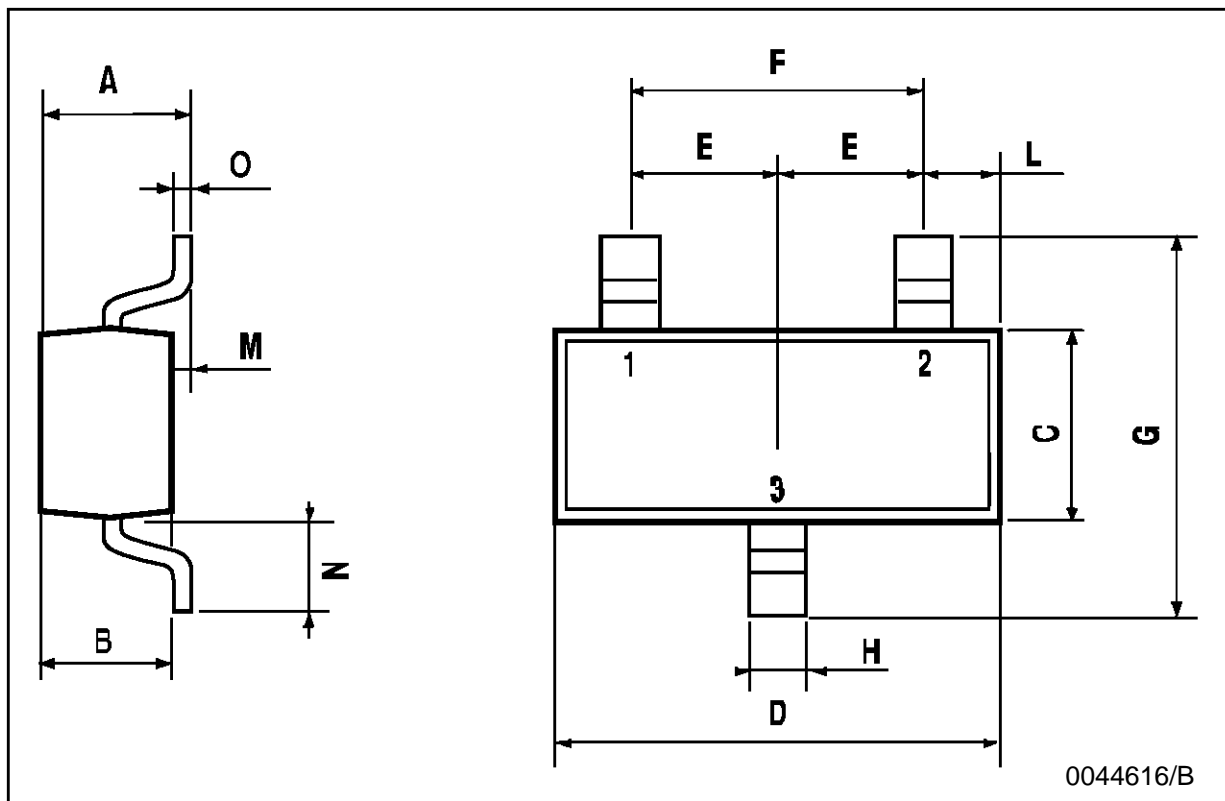
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = -20\text{ V}$ $V_{CB} = -20\text{ V}$ $T_j = 100^{\circ}\text{C}$			-100 -10	nA μA
$V_{(BR)CES}^*$	Collector-Emitter Breakdown Voltage ($V_{BE} = 0$)	$I_C = -10\ \mu\text{A}$	-50			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -2\ \text{mA}$	-45			V
$V_{(BR)CBO}^*$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = -10\ \mu\text{A}$	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = -10\ \mu\text{A}$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -10\ \text{mA}$ $I_B = -0.5\ \text{mA}$ $I_C = -50\ \text{mA}$ $I_B = -2.5\ \text{mA}$		-0.18	-0.3	V V
$V_{BE(sat)}^*$	Collector-Base Saturation Voltage	$I_C = -10\ \text{mA}$ $I_B = -0.5\ \text{mA}$ $I_C = -50\ \text{mA}$ $I_B = -2.5\ \text{mA}$		-0.72 -0.81		V V
$V_{BE(on)}^*$	Base-Emitter On Voltage	$I_C = -2\ \text{mA}$ $V_{CE} = -5\ \text{V}$	-0.6		-0.75	V
h_{FE}^*	DC Current Gain	for BCW69 $I_C = -10\ \mu\text{A}$ $V_{CE} = -5\ \text{V}$ $I_C = -2\ \text{mA}$ $V_{CE} = -5\ \text{V}$ for BCW70 $I_C = -10\ \mu\text{A}$ $V_{CE} = -5\ \text{V}$ $I_C = -2\ \text{mA}$ $V_{CE} = -5\ \text{V}$	120 215	90 150	260 500	
f_T	Transition Frequency	$I_C = -10\ \text{mA}$ $V_{CE} = -5\ \text{V}$ $f = 100\ \text{MHz}$		150		MHz
C_{CB}	Collector Base Capacitance	$I_E = 0$ $V_{CB} = -10\ \text{V}$ $f = 1\ \text{MHz}$			7	dB
NF	Noise Figure	$I_C = -0.2\ \text{mA}$ $V_{CE} = -5\ \text{V}$ $f = 1\ \text{KHz}$ $\Delta f = 200\ \text{Hz}$ $R_g = 2\ \text{K}\Omega$			10	dB

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1995 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A